- Independent Asynchronous Inputs and **Outputs**
- 64 Words by 9 Bits
- Data Rates From 0 to 40 MHz
- Fall-Through Time . . . 20 ns Typical
- 3-State Outputs

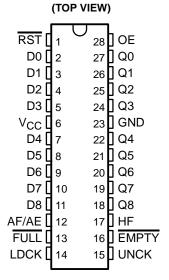
### description

This 576-bit memory uses advanced low-power Schottky IMPACT-X<sup>™</sup> technology and features high speed and fast fall-through times. It is organized as 64 words by 9 bits.

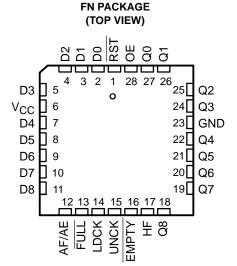
A FIFO memory is a storage device that allows data to be written into and read from its array at independent data rates. The function is used as a buffer to couple two buses operating at different clock rates. This FIFO is designed to process data at rates from 0 to 40 MHz in a bit-parallel format, word by word.

Data is written into memory on a low-to-high transition of the load clock (LDCK) input and is read out on a low-to-high transition of the unload clock (UNCK) input. The memory is full when the number of words clocked in exceeds by 64 the number of words clocked out. When the memory is full, LDCK signals have no effect on the data residing in memory. When the the memory is empty, UNCK signals have no effect.

Status of the FIFO memory is monitored by the FULL, EMPTY, almost-full/almost-empty (AF/AE), and half-full (HF) output flags. The FULL output is low when the memory is full and high when the memory is not full. The EMPTY output is low when the memory is empty, and high when it is not



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empty. The AF/AE flag is high when the FIFO contains eight or less words or 56 or more words. The AF/AE flag is low when the FIFO contains between nine and 55 words. The HF flag is high when the FIFO contains 32 or more words and is low when the FIFO contains 31 words or less.

A low level on the reset (RST) input resets the internal stack control pointers and also sets EMPTY low and FULL high. The outputs are not reset to any specific logic levels. The first low-to-high transition on LDCK, either after a RST pulse or from an empty condition, causes EMPTY to go high and the data to appear on the Q outputs. The first word does not have to be unloaded. Data outputs are noninverting with respect to the data inputs and are at a high-impedance state when the output-enable (OE) input is low. The OE input does not effect either the FULL or EMPTY output flags. Cascading is easily accomplished in the word-width direction, but is not possible in the word-depth direction.

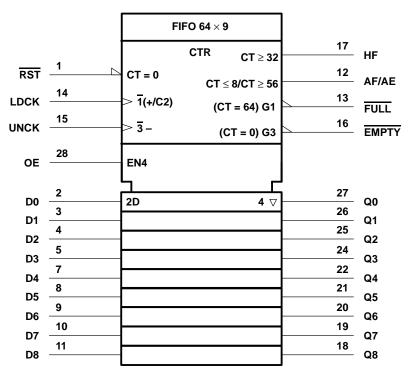
The SN74ALS2233A is characterized for operation from 0°C to 70°C.



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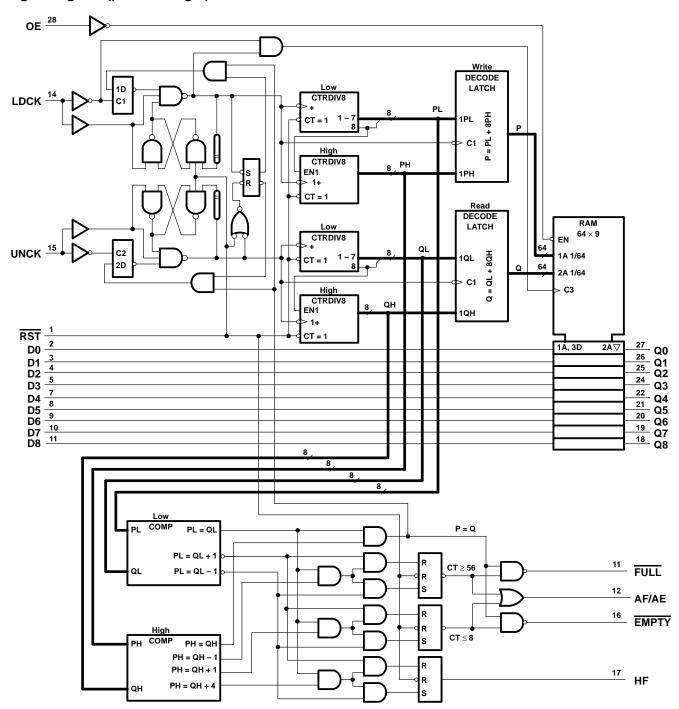
### logic symbol<sup>†</sup>

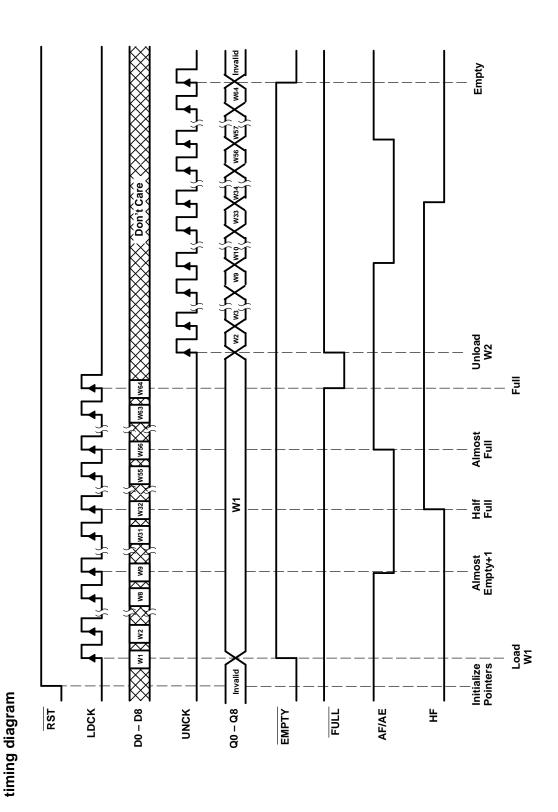


<sup>†</sup> This symbol is in accordance with ANSI/IEEE Standard 91-1984 and IEC Publication 617-12. The symbol is functionally accurate but does not show the details of implementation; for these, see the logic diagram. The symbol represents the memory as if it were controlled by a single counter whose content is the number of words stored at the time. Output data is invalid when the counter content (CT) is 0.



### logic diagram (positive logic)







# SN74ALS2233A $64 \times 9$ ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

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### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V <sub>CC</sub> (see Note 1)	
Input voltage	
Voltage applied to a disabled 3-state output	
Operating free-air temperature range, $T_A$	0°C to 70°C
Storage temperature range	

### recommended operating conditions

			MIN	NOM	MAX	UNIT	
Vcc	Supply voltage			5	5.5	V	
$V_{IH}$	High-level input voltage					V	
$V_{IL}$	Low-level input voltage				0.8	V	
1	Lligh lovel output output	Q outputs			-2.6	mA	
ЮН	High-level output current	Flag outputs			-0.4		
loL	Low-level output current	Q outputs			24	A	
		Flag outputs			8	mA	
fclock	Clock frequency	LDCK, UNCK	0		40	MHz	
		RST low	25				
	Pulse duration	LDCK low	13			ns	
t <sub>W</sub>		LDCK high	12				
		UNCK low	13				
		UNCK high	12				
t <sub>su1</sub>	Setup time, data before LDCK↑					ns	
t <sub>su2</sub>	Setup time, RST high (inactive) before LDCK↑					ns	
t <sub>h</sub>	Hold time, data after LDCK↑					ns	
T <sub>A</sub>	Operating free-air temperature				70	°C	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond those indicated in the "recommended operating conditions" section of this specification is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to GND.

# SN74ALS2233A $64 \times 9$ ASYNCHRONOUS FIRST-IN, FIRST-OUT MEMORY

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# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS <sup>†</sup>		MIN	TYP <sup>‡</sup>	MAX	UNIT	
VIK		V <sub>CC</sub> = 4.5 V,	$I_{I} = -18 \text{ mA}$				-1.2	V
Vон	Q outputs	$V_{CC} = 4.5 \text{ V},$	$I_{OH} = -2.6 \text{ mA}$		2.4	3.2		V
	Flag outputs	$V_{CC} = MIN \text{ to MAX},$	I <sub>OH</sub> = 0.4 mA		V <sub>CC</sub> -2			V
V <sub>OL</sub>	Q outputs	V <sub>CC</sub> = 4.5 V	I <sub>OL</sub> = 12 mA			0.25	0.4	
			I <sub>OL</sub> = 24 mA			0.35	0.5	V
	Flag outputs	ag outputs V <sub>CC</sub> = 4.5 V	I <sub>OL</sub> = 4 mA			0.25	0.4	] <sup>v</sup>
			I <sub>OL</sub> = 8 mA			0.35	0.5	
lozh	-	$V_{CC} = 5.5 \text{ V},$	V <sub>O</sub> = 2.7 V				20	μΑ
lozL		V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 0.4 V				-20	μΑ
lį		V <sub>CC</sub> = 5.5 V,	V <sub>I</sub> = 7 V				0.1	mA
lіН		V <sub>CC</sub> = 5.5 V,	V <sub>I</sub> = 2.7 V				20	μΑ
ΊL	CLKs	V <sub>CC</sub> = 5.5 V,	∧l =Ω;≒, ∧		-	-0.2	mA	
	Others					-0.1		
I <sub>O</sub> §	Q outputs	V <sub>CC</sub> = 5.5 V,	V <sub>O</sub> = 2.25 V		-20		-130	A
	Flag outputs				-20		-112	mA
ICC		V <sub>CC</sub> = 5.5 V				175	290	mA

<sup>†</sup> For conditions shown as MIN or MAX, use the appropriate value specified under recommended operating conditions.

<sup>‡</sup> All typical values are at  $V_{CC} = 5 \text{ V}$ ,  $T_A = 25^{\circ}\text{C}$ .

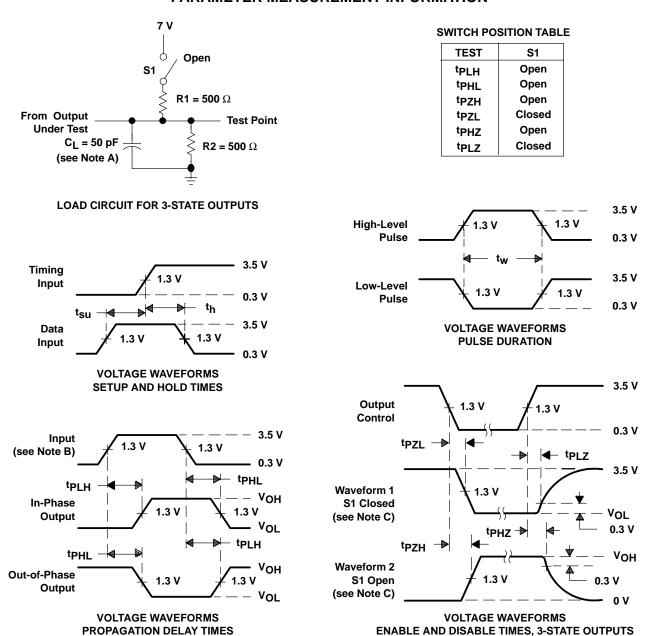
<sup>§</sup> The output conditions have been chosen to produce a current that closely approximates one half of the true short-circuit output current, IOS.

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## switching characteristics (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	$V_{CC} = 5 \text{ V},$ $C_L = 50 \text{ pF},$ $R1 = 500 \Omega,$ $R2 = 500 \Omega,$ $T_A = 25^{\circ}\text{C}$ $MIN  TYP  MAX$		F, 2, 2,	V <sub>CC</sub> = 4.5 C <sub>L</sub> = 50 pF R1 = 500 Ω R2 = 500 Ω T <sub>A</sub> = 0°C to	2, 2,	UNIT	
f <sub>max</sub>	LDCK, UNCK		IVIIIV	111	IVIAA	40	IVIAA	MHz	
Пах	LDCK↑	Any Q		18	26		30	ns	
<sup>t</sup> pd	UNCK↑			18	24		27		
t <sub>PLH</sub>	LDCK↑			12	16		18	ns	
tPHL	UNCK↑	EMPTY		12	17		20		
<sup>t</sup> PHL	RST↓	EMPTY		12	17		20	ns	
tPHL	LDCK↑	FULL		16	21		22	ns	
<b>4</b>	UNCK↑	FULL		10	15		18	ns	
<sup>t</sup> PLH	RST↓			13	19		23		
<sup>t</sup> PLH	LDCK↑	AF/AE		22	27		30	ns	
<sup>t</sup> PHL	LDCK1	AF/AE		19	25		28	115	
<sup>t</sup> PLH	UNCK↑	AF/AE		22	27		30	ns	
<sup>t</sup> PHL		AF/AL		17	23		26	113	
<sup>t</sup> PLH	RST↓	AF/AE		12	16		18	ns	
<sup>t</sup> PLH	LDCK↑	HF		22	27		30		
<sup>t</sup> PHL	RST↓	ПF		28	32		35	ns	
<sup>t</sup> PHL	UNCK↑	HF		16	22		25	ns	
t <sub>en</sub>	OE↑	Q		11	15		17	ns	
<sup>t</sup> dis	OE↓	Q		11	17		19	ns	

#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

- B. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_0 = 50 \Omega$ ,  $t_f \leq$  2 ns,  $t_f \leq$  2 ns.
- C. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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